Part Number Customer					
Category	Parameter		Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm		
	2.0	Primary Flat Orientation	{110}+/- 1.0 degree	Wafer Vendor	
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor	
	4.0	Secondary Flat Orientation	none/semi standard		
	5.0	Secondary Flat Length	none / 18.5 +/- 2.5mm	Wafer Vendor	
	6.0	Overall Thickness	321.50 +/- 6.00 μm	ADE, 100%	
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process	
	8.0	Bow	<60.00µm	ADE to ASTM F534, 20%	
	9.0	Warp	<60.00µm	ADE to ASTM F657, 20%	
	10.0	Edge Chips	0	Bright Light, 100% (note 2)	
	11.0	Edge Exclusion	5mm		
	12.0	Backside Laser Marking Type	On wafer BACKSIDE. Scribe format: [KEYSTONE.XXXX] (unique scribe)	Guaranteed by process	
HandleSilicon	13.0	Handle Growth Method	CZ	Wafer Vendor	
	14.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	15.0	Handle Thickness	300.00 +/- 5.00 μm	ADE, 100%	
	16.0	Handle Doping Type	Ν	Wafer Vendor	
	17.0	Handle Dopant	Antimony	Wafer Vendor	
	18.0	Handle Resistivity	0.01 - 0.025 Ohmem	Wafer Vendor	
	19.0	Backside Finish	Polished with lasermarking and oxide.	Wafer Vendor	
BuriedOxide	20.0	Oxide Type	Thermal		
	21.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%	
	22.0	Oxide formed on	Handle Wafer		
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor	
	24.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	25.0	Nominal Thickness	19.50 +/- 0.50 μm	FTIR, 100% 9-Pt (note3)	
	26.0	Distance to device silicon edge from wafer edge	<= 2.0 mm	Typical by process	
	27.0	Device Doping Type	Ν	Wafer Vendor	
	28.0	Device Dopant	Antimony	Wafer Vendor	
	29.0	Device Resistivity	0.01 - 0.025 Ohmem	Wafer Vendor	
	30.0	Voids	0	Bright Light, 100% (note 2)	
	31.0	Scratches	0	Bright Light, 100% (note 2)	
	32.0	Haze	none	Bright Light, 100% (note 2)	

Icemos Technology Ltd

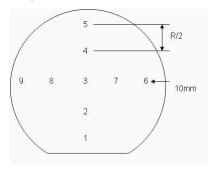
Product Specification

1000.538902

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspect	tion performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information